

■ PRODUCT CHARACTERISTICS

VDSS	650
R _{DS(on)} Typ(@V _{GS} = 10 V)	0.66Ω
Qg@typ	36nC
ID	13A

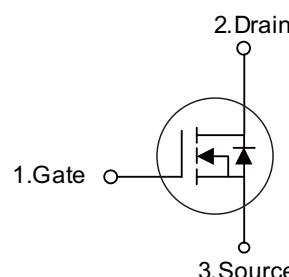
■ APPLICATIONS

- High efficiency switch mode power supplies
- Electronic ballasts
- LED power supply

■ FEATURES

- * Fast switching capability
- * Avalanche energy tested
- * Improved dv/dt capability, high ruggedness

Symbol



TO-220



TO-220F

■ ORDER INFORMATION

Order codes		Package	Packing
Halogen-Free	Halogen		
N/A	MOT13N65HF	TO-220F	50 pieces/Tube
N/A	MOT13N65A	TO-220	50 pieces/Tube

■ ABSOLUTE MAXIMUM RATINGS (T_C = 25°C, unless otherwise specified)

PARAMETER	SYMBOL	RATINGS	UNIT
Drain-Source Voltage	V _{DSS}	650	V
Gate-Source Voltage	V _{GSS}	±30	V
Continuous Drain Current	I _D	13	A
Pulsed Drain Current (Note 2)	I	26	A
Avalanche Energy	E _{AS}	255	mJ
Peak Diode Recovery dv/dt (Note 4)	dv/dt	2.9	V/ns
Power Dissipation	TO-220	P _D	160
			42
Junction Temperature	T _J	+150	°C
Storage Temperature	T _{STG}	-55 ~ +150	°C

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

2. Repetitive Rating: Pulse width limited by maximum junction temperature.

3. L = 1.0mH, I_{AS} = 22.6A, V_{DD} = 50V, R_G = 25 Ω, Starting T_J = 25°C

4. I_{SD} ≤ 13A, di/dt ≤ 200A/μs, V_{DD} ≤ BV_{DSS}, Starting T_J = 25°C

■ THERMAL DATA

PARAMETER	SYMBOL	RATINGS	UNIT
Junction to Ambient	θ _{JA}	62.5	°C/W
Junction to Case	TO-220	0.78	°C/W
		2.98	°C/W

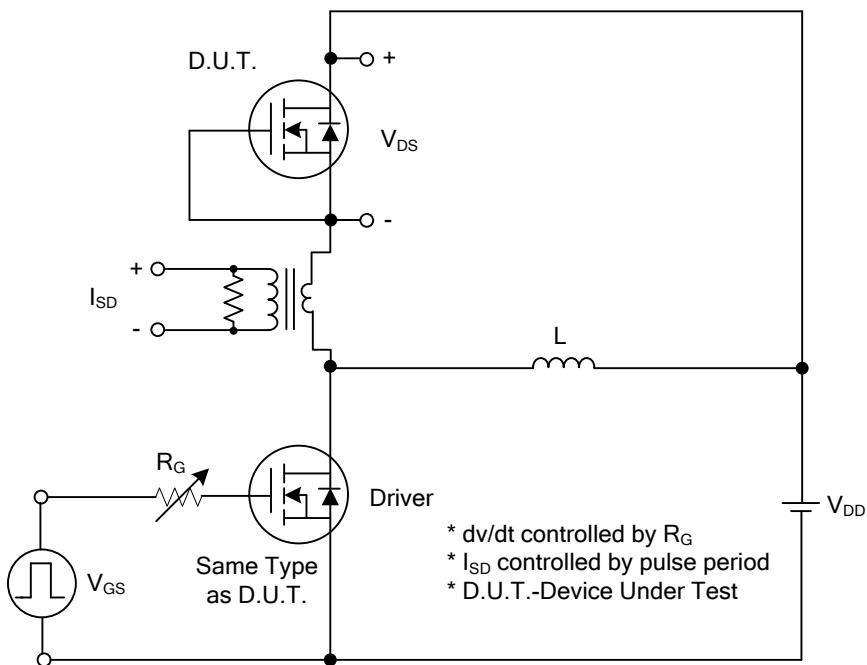
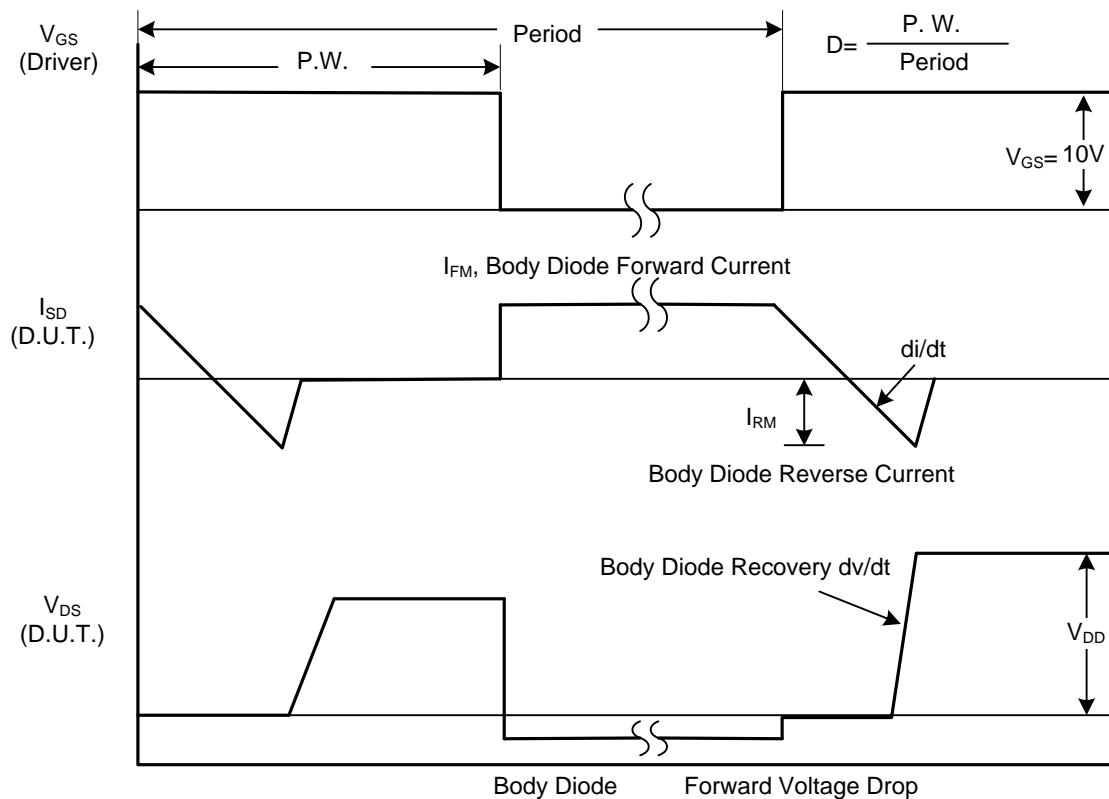
■ ELECTRICAL CHARACTERISTICS ($T_C=25^\circ\text{C}$, unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Off characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{\text{GS}}=0\text{V}, I_{\text{D}}=250\mu\text{A}$	650	-	-	V
Drain-Source Leakage Current	I_{DSS}	$V_{\text{DS}}=650\text{V}, V_{\text{GS}}=0\text{V}$	-	-	1	μA
Gate- Source Leakage Current	Forward	$V_{\text{GS}}=30\text{V}, V_{\text{DS}}=0\text{V}$	-	-	100	nA
	Reverse	$V_{\text{GS}}=-30\text{V}, V_{\text{DS}}=0\text{V}$	-	-	-100	nA
On characteristics						
Gate Threshold Voltage	$V_{\text{GS}(\text{TH})}$	$V_{\text{DS}}=V_{\text{GS}}, I_{\text{D}}=250\mu\text{A}$	2.0	-	4.0	V
Static Drain-Source On-State Resistance	$R_{\text{DS}(\text{ON})}$	$V_{\text{GS}}=10\text{V}, I_{\text{D}}=6.5\text{A}$	-	0.66	0.7	Ω
Dynamic characteristics						
Input Capacitance	C_{ISS}	$V_{\text{DS}}=25\text{V}, V_{\text{GS}}=0\text{V}, f=1.0\text{MHz}$	-	1700	-	pF
Output Capacitance	C_{OSS}		-	156	-	pF
Reverse Transfer Capacitance	C_{RSS}		-	11	-	pF
Switching characteristics						
Total Gate Charge (Note 1)	Q_G	$V_{\text{DS}}=520\text{V}, V_{\text{GS}}=10\text{V}, I_{\text{D}}=13\text{A}$ $I_G=1\text{mA}$ (Note 1, 2)	-	36	-	nC
Gate-Source Charge	Q_{GS}		-	9	-	nC
Gate-Drain Charge	Q_{GD}		-	9.4	-	nC
Turn-On Delay Time (Note 1)	$t_{\text{D}(\text{ON})}$	$V_{\text{DS}}=100\text{V}, V_{\text{GS}}=10\text{V}, I_{\text{D}}=13\text{A},$ $R_G=25\Omega$ (Note 1, 2)	-	28	-	ns
Turn-On Rise Time	t_R		-	22	-	ns
Turn-Off Delay Time	$t_{\text{D}(\text{OFF})}$		-	108	-	ns
Turn-Off Fall Time	t_F		-	37	-	ns
Drain-source diode characteristics						
Maximum Body-Diode Continuous Current	I_S		-	-	13	A
Maximum Body-Diode Pulsed Current	I_{SM}		-	-	26	A
Drain-Source Diode Forward Voltage (Note 1)	V_{SD}	$I_S=13\text{A}, V_{\text{GS}}=0\text{V}$	-	-	1.4	V
Reverse Recovery Time (Note 1)	t_{rr}	$I_S=13\text{A}, V_{\text{GS}}=0\text{V}$	-	410	-	ns
Reverse Recovery Charge	Q_{rr}	$dI/dt=100\text{A}/\mu\text{s}$	-	12.8	-	μC

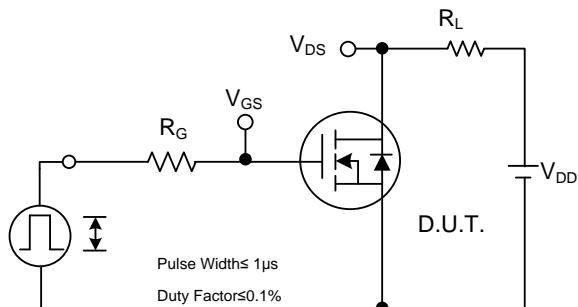
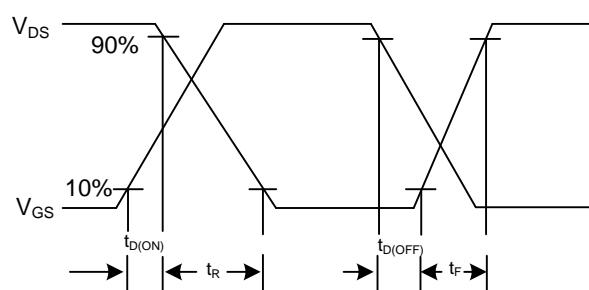
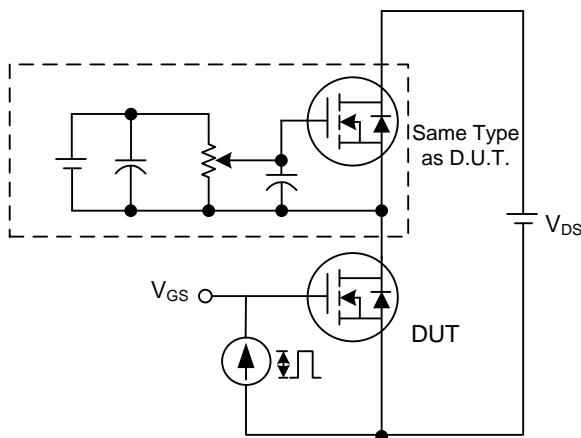
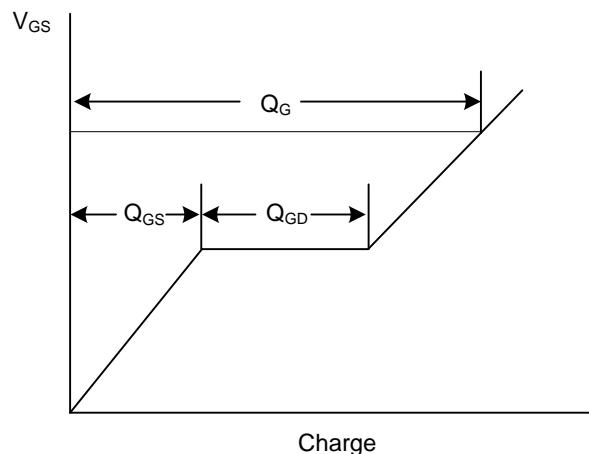
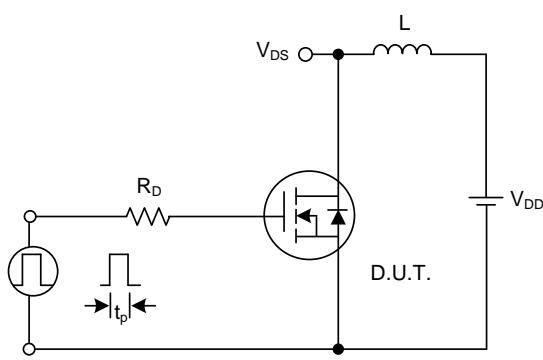
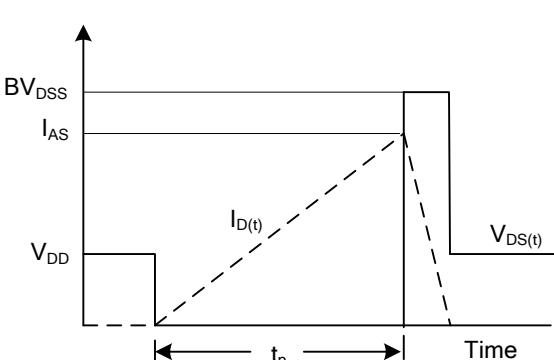
Notes: 1. Pulse Test: Pulse width $\leq 300\mu\text{s}$, Duty cycle $\leq 2\%$.

2. Essentially independent of operating temperature.

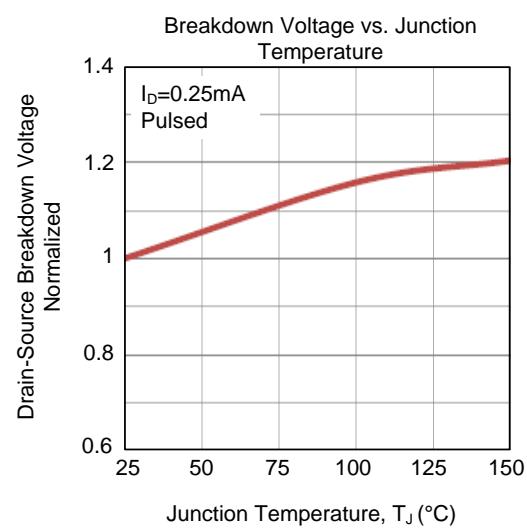
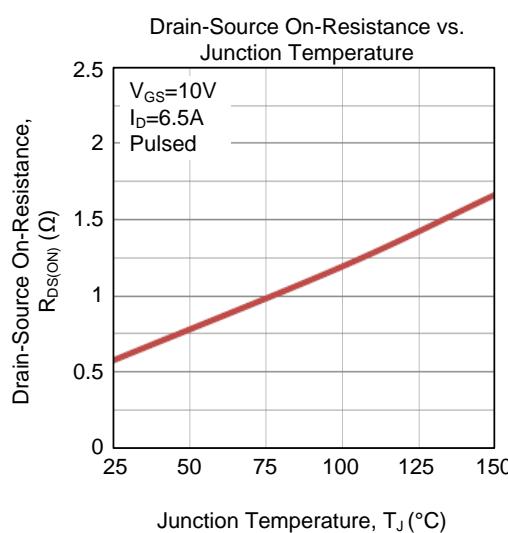
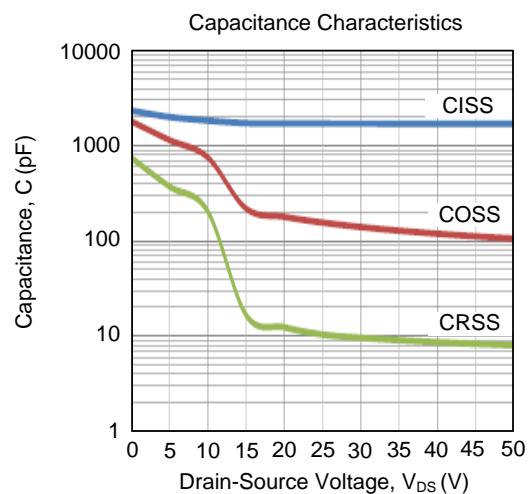
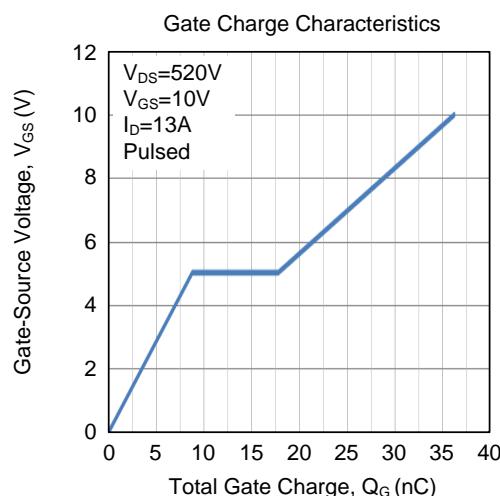
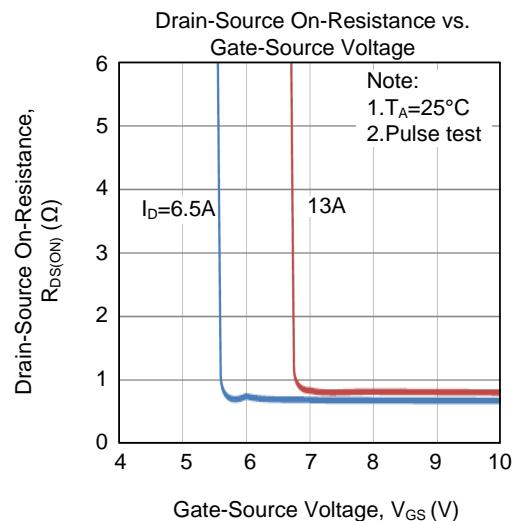
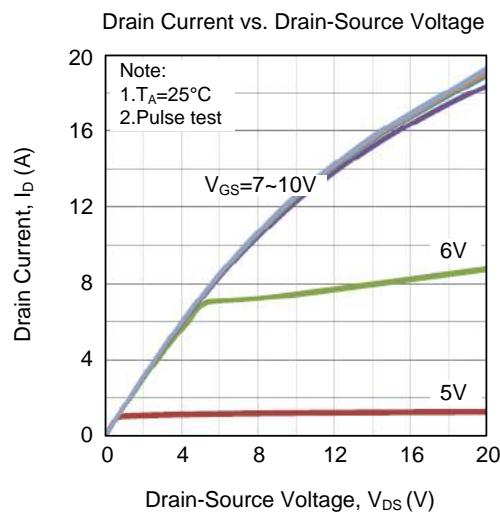
■ TEST CIRCUITS AND WAVEFORMS

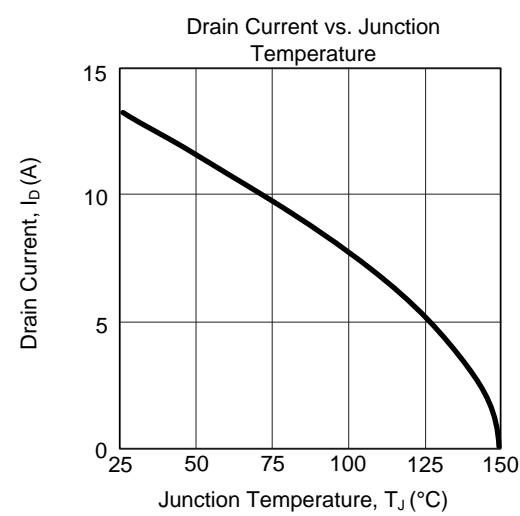
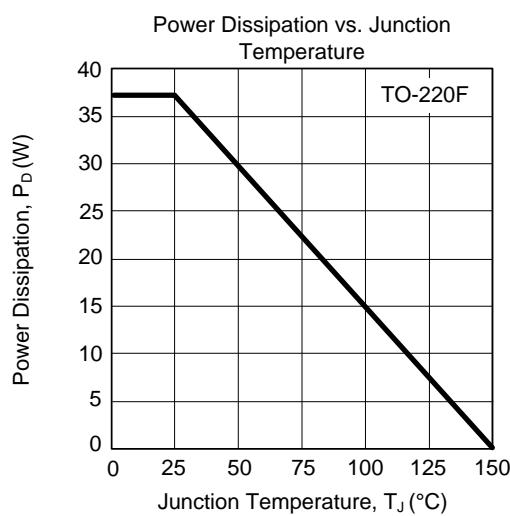
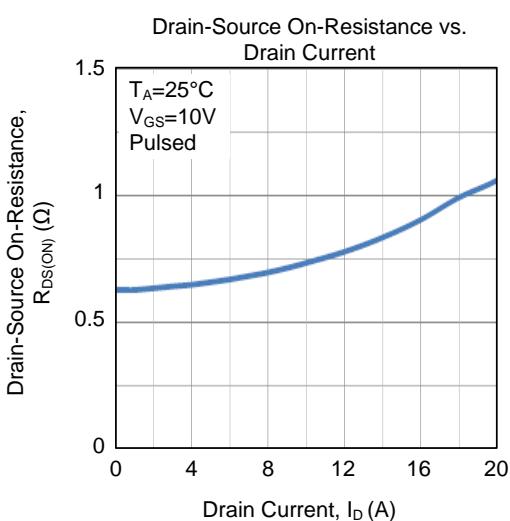
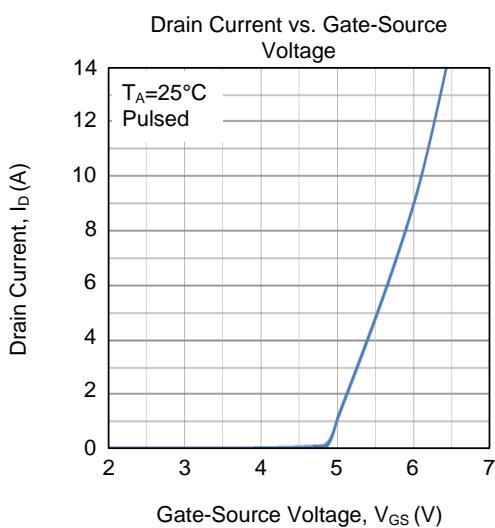
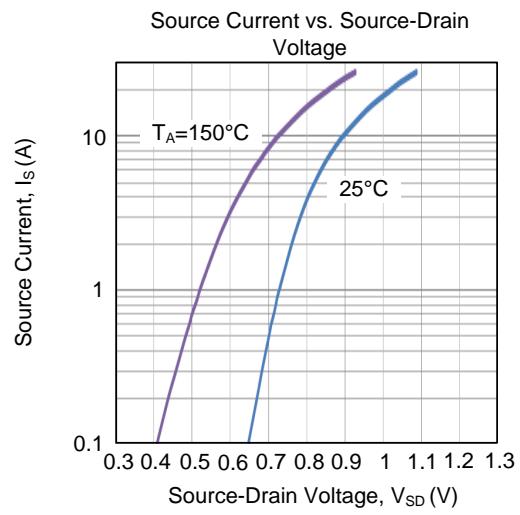
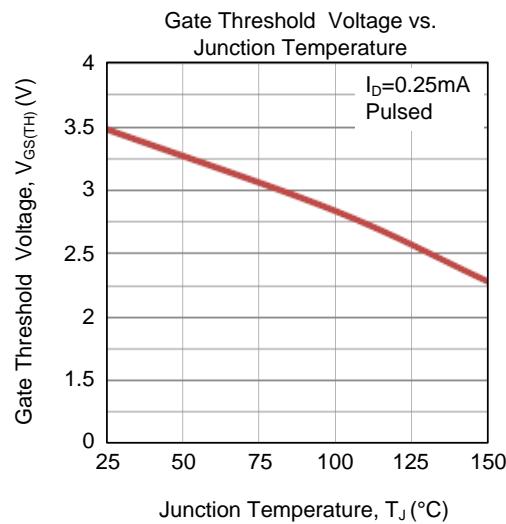

Peak Diode Recovery dv/dt Test Circuit

Peak Diode Recovery dv/dt Waveforms

■ TEST CIRCUITS AND WAVEFORMS(Cont.)

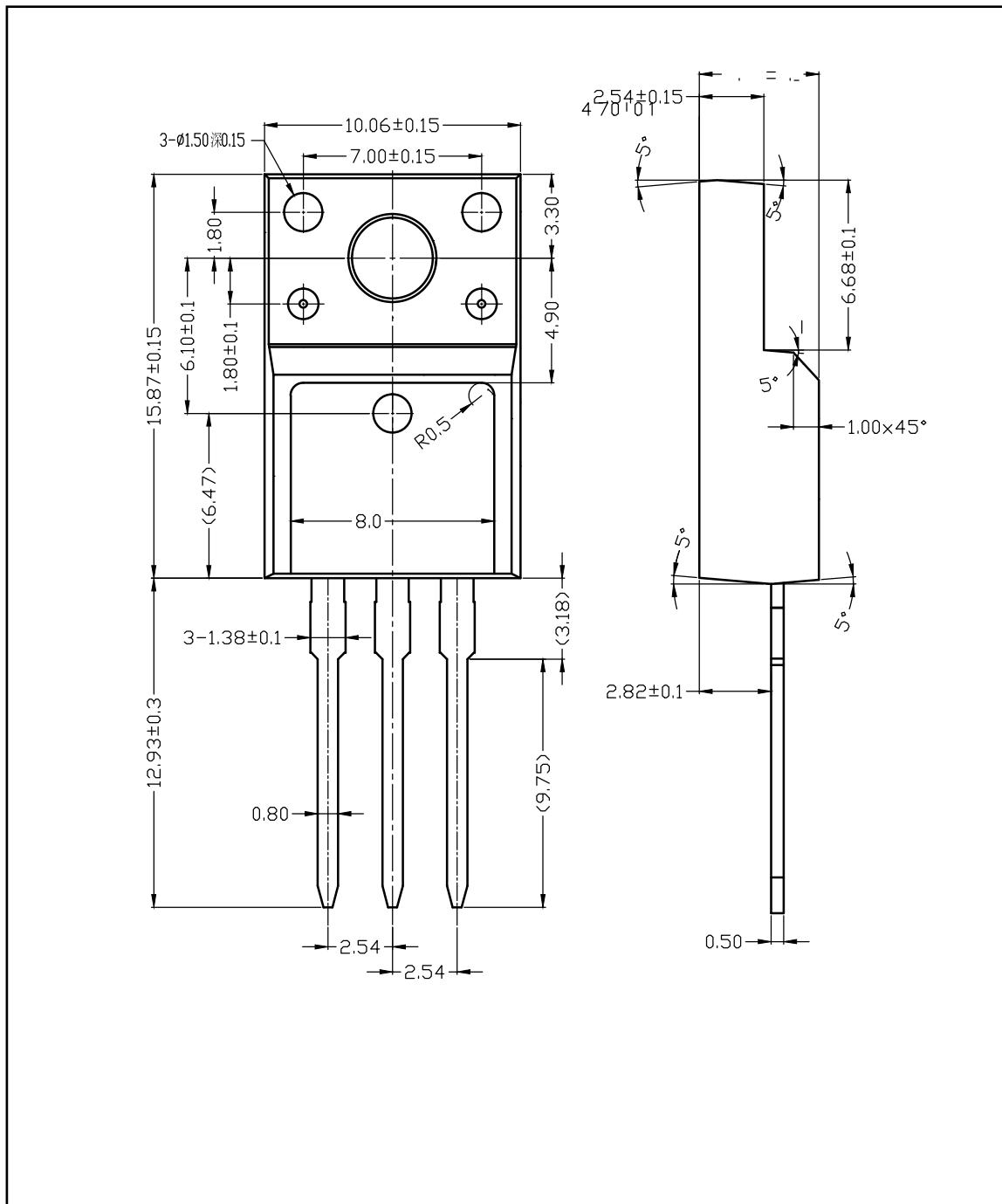

Switching Test Circuit

Switching Waveforms

Gate Charge Test Circuit

Gate Charge Waveform

Unclamped Inductive Switching Test Circuit

Unclamped Inductive Switching Waveforms

■ TYPICAL CHARACTERISTICS



■ TYPICAL CHARACTERISTICS(Cont.)


■ TO-220F-3L PACKAGE OUTLINE DIMENSIONS



■ TO-220-3L PACKAGE OUTLINE DIMENSIONS

